

ABSTRACT

A semiconductor memory device is disclosed. The semiconductor memory device may include a bit line extending in a first direction, first and second active patterns disposed on the bit line, a back-gate electrode, which is disposed between the first and second active patterns and is extended in a second direction to cross the bit line, a first word line, which is provided at a side of the first active pattern and is extended in the second direction, a second word line, which is provided at an opposite side of the second active pattern and is extended in the second direction, and contact patterns coupled to the first and second active patterns, respectively.

FIG. 1B